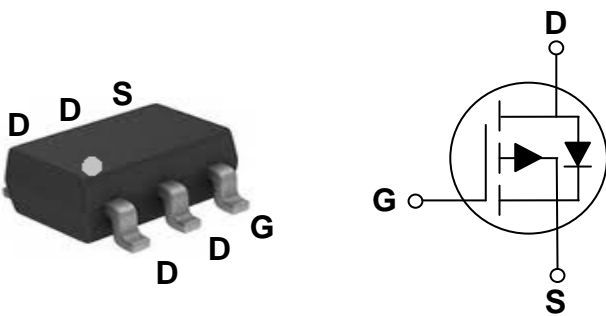


General Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

SOT23-6 Pin Configuration



BVDSS	RDSON	ID
-20V	26mΩ	-6.5A

Features

- -20V, -6.5A, $R_{DS(ON)} = 26m\Omega @ V_{GS} = -4.5V$
- Improved dv/dt capability
- Fast switching
- Green Device Available
- Suit for -1.8V Gate Drive Applications

Applications

- Notebook
- Load Switch
- Networking



Absolute Maximum Ratings $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 10	V
I_D	Drain Current – Continuous ($T_c=25^\circ C$)	-6.5	A
	Drain Current – Continuous ($T_c=100^\circ C$)	-4.1	A
I_{DM}	Drain Current – Pulsed ¹	-26	A
P_D	Power Dissipation ($T_c=25^\circ C$)	1.56	W
	Power Dissipation – Derate above $25^\circ C$	0.012	W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	80	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.01	---	$V/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-20V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-16V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	-10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 10V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-4.5V, I_D=-5A$	---	21	26	m Ω
		$V_{GS}=-2.5V, I_D=-4A$	---	26	32	
		$V_{GS}=-1.8V, I_D=-3A$	---	32	40	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.3	-0.6	-1.0	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	3	---	$\text{mV}/^\circ\text{C}$
gfs	Forward Transconductance	$V_{DS}=-10V, I_S=-5A$	---	15	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge ^{2,3}	$V_{DS}=-10V, V_{GS}=-4.5V, I_D=-5A$	---	19.5	29	nC
Q_{gs}	Gate-Source Charge ^{2,3}		---	2	4	
Q_{gd}	Gate-Drain Charge ^{2,3}		---	3.6	7	
$T_{d(on)}$	Turn-On Delay Time ^{2,3}	$V_{DD}=-10V, V_{GS}=-4.5V, R_G=25\Omega$ $I_D=-1A$	---	10.4	20	nS
T_r	Rise Time ^{2,3}		---	37.5	71	
$T_{d(off)}$	Turn-Off Delay Time ^{2,3}		---	89.1	129	
T_f	Fall Time ^{2,3}		---	24.6	47	
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, F=1\text{MHz}$	---	1670	2430	pF
C_{oss}	Output Capacitance		---	220	320	
C_{rss}	Reverse Transfer Capacitance		---	120	180	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	-6.5	A
I_{SM}	Pulsed Source Current		---	---	-26	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

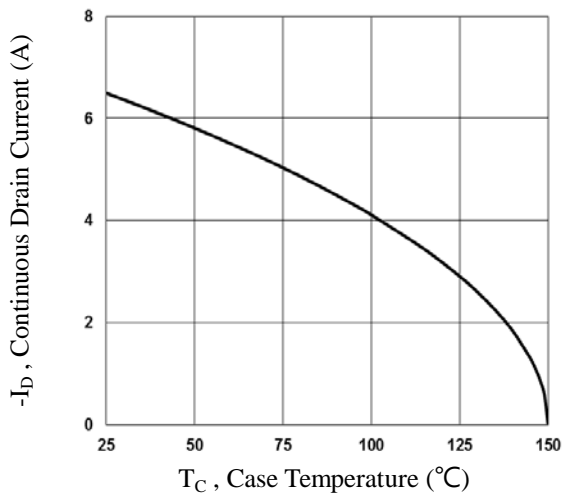


Fig.1 Continuous Drain Current vs. T_C

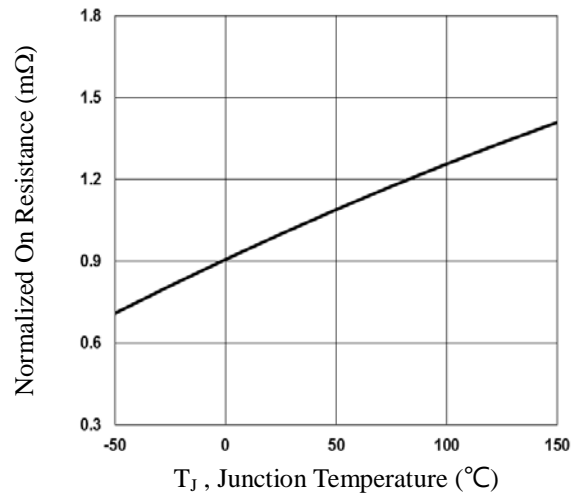


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

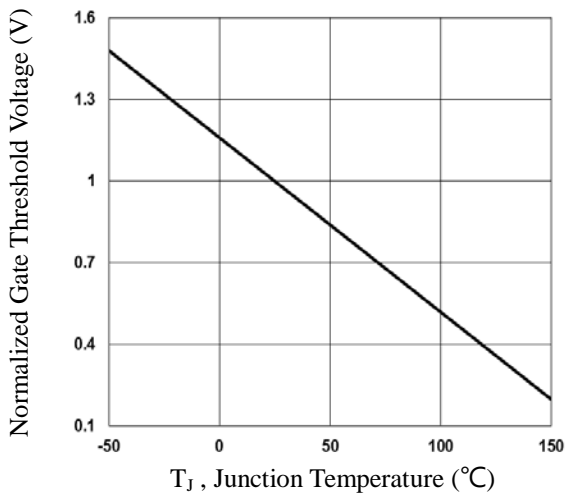


Fig.3 Normalized V_{th} vs. T_J

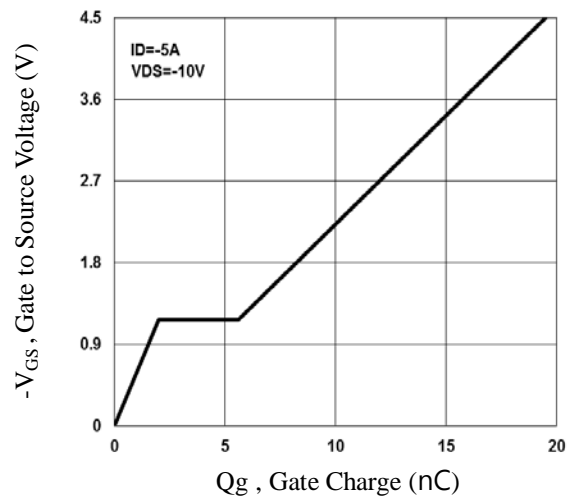


Fig.4 Gate Charge Waveform

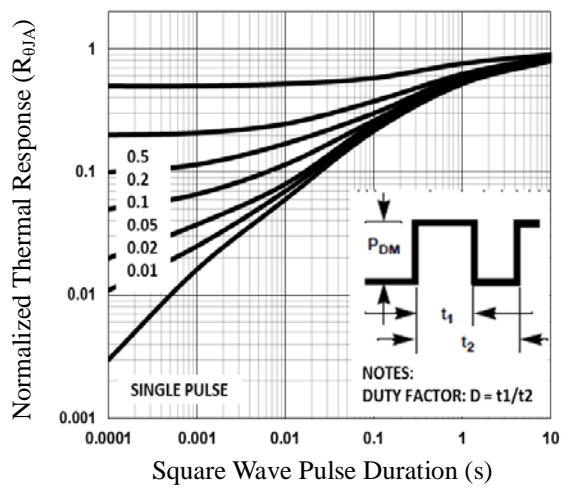


Fig.5 Normalized Transient Impedance

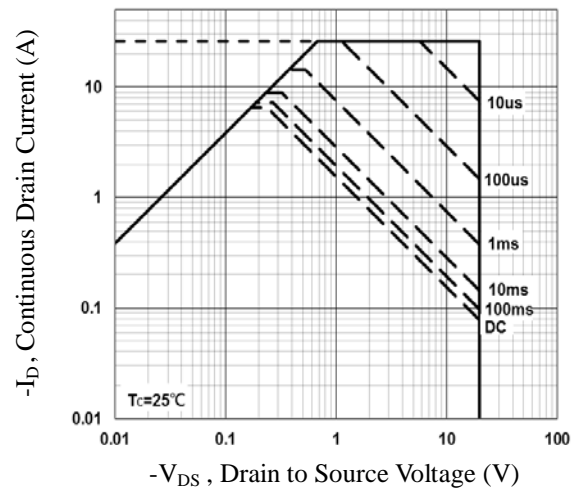


Fig.6 Maximum Safe Operation Area

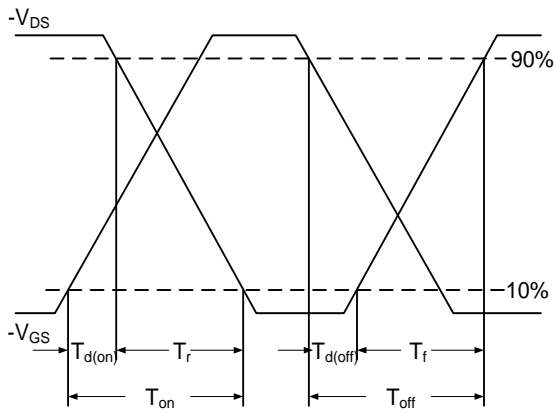


Fig.7 Switching Time Waveform

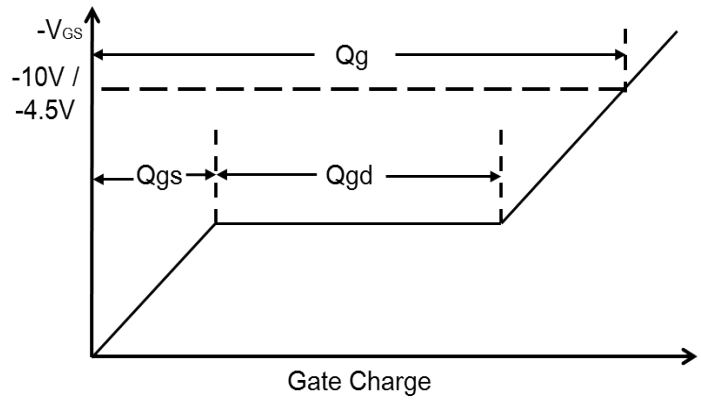
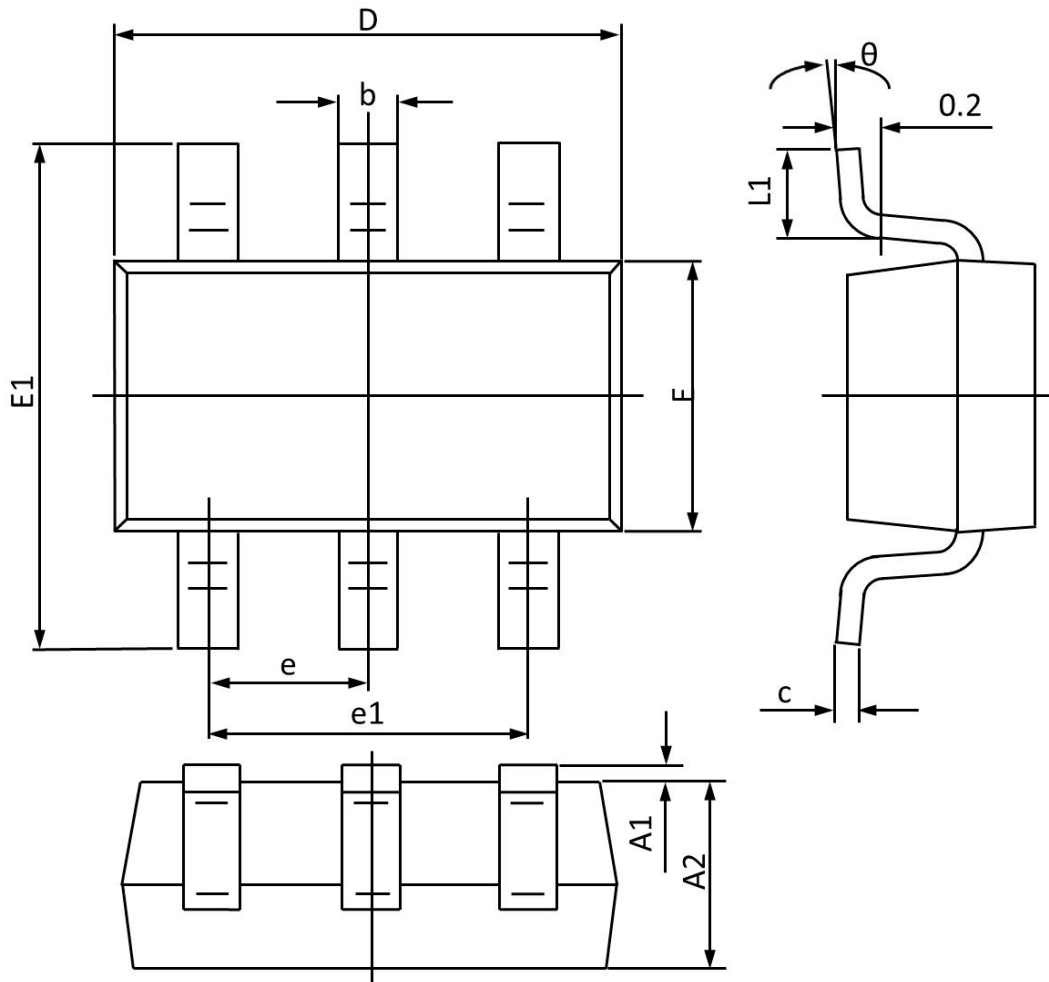


Fig.8 Gate Charge Waveform



SOT23-6 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A1	0.000	0.100	0.000	0.004
A2	1.000	1.200	0.040	0.047
b	0.300	0.500	0.012	0.019
c	0.047	0.207	0.002	0.008
D	2.800	3.000	0.110	0.118
E1	2.600	3.000	0.103	0.118
e	0.950 TYP		0.037 TYP	
e1	1.900 TYP		0.075 TYP	
L1	0.250	0.550	0.010	0.021
θ	0°	8°	0°	8°